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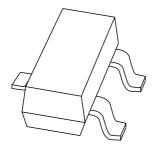
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



BC859; BC860 PNP general purpose transistors

Product data sheet Supersedes data of 1999 May 28 2004 Jan 16



PNP general purpose transistors

BC859; BC860

FEATURES

• Low current (max. 100 mA)

• Low voltage (max. 45 V).

APPLICATIONS

• Low noise input stages of audio frequency equipment.

DESCRIPTION

PNP transistor in a SOT23 plastic package. NPN complements: BC849 and BC850.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾	TYPE NUMBER	MARKING CODE ⁽¹⁾	
BC859B	4B*	BC860B	4F*	
BC859C	4C*	BC860C	4G*	

Note

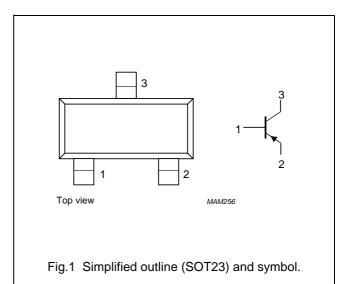
1. * = p: Made in Hong Kong.

* = t : Made in Malaysia.

* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE	PACKAGE			
NUMBER	NAME	DESCRIPTION	VERSION	
BC859B	_	plastic surface mounted package; 3 leads	SOT23	
BC859C				
BC860B				
BC860C				

PNP general purpose transistors

BC859; BC860

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BC859		_	-30	V
	BC860		_	-50	V
V _{CEO}	collector-emitter voltage	open base			
	BC859		_	-30	V
	BC860		_	-45	V
V _{EBO}	emitter-base voltage	open collector	-	- 5	V
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

^{1.} Transistor mounted on an FR4 printed-circuit board.

PNP general purpose transistors

BC859; BC860

CHARACTERISTICS

 $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -30 \text{ V}$	_	-1	-15	nA
		I _E = 0; V _{CB} = -30 V; T _j = 150 °C	_	_	-4	μΑ
I _{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5 \text{ V}$	_	_	-100	nA
h _{FE}	DC current gain BC859B; BC860B BC859C; BC860C	$I_C = -2$ mA; $V_{CE} = -5$ V; see Figs 2 and 3	220 420	_	475 800	
V _{CEsat}	collector-emitter saturation	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	-75	-300	mV
	voltage	$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}$	_	-250	-650	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA}$; $I_B = -0.5 \text{ mA}$; note 1	_	-700	_	mV
		$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}; \text{ note 1}$	_	-850	_	mV
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA}$; $V_{CE} = -5 \text{ V}$; note 2	-600	-650	-750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}; \text{ note 2}$	_	_	-820	mV
C _c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = -10 \text{ V}$; $f = 1 \text{ MHz}$	=	4.5	=	pF
Ce	emitter capacitance	$I_C = I_c = 0$; $V_{EB} = -500 \text{ mV}$; $f = 1 \text{ MHz}$	_	10	_	pF
f _T	transition frequency	$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}; f = 100 \text{ MHz}$	100	_	=	MHz
F	noise figure BC859B; BC860B; BC859C; BC860C	I_C = -200 μA; V_{CE} = -5 V; R_S = 2 kΩ; f = 30 Hz to 15 kHz	_	_	4	dB
	noise figure BC859B; BC860B; BC859C; BC860C	I_C = -200 μA; V_{CE} = -5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	_	_	4	dB

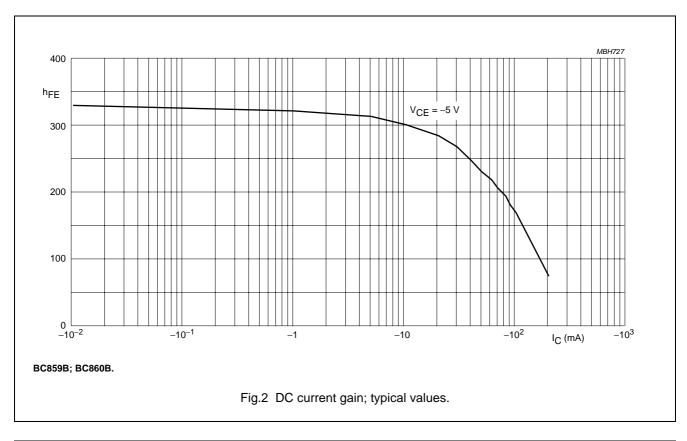
Notes

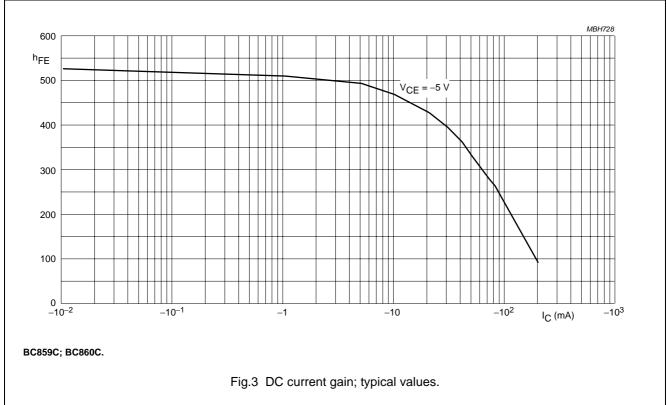
- 1. V_{BEsat} decreases by about $-1.7\ mV/K$ with increasing temperature.
- 2. V_{BE} decreases by about -2 mV/K with increasing temperature.

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PNP general purpose transistors

BC859; BC860





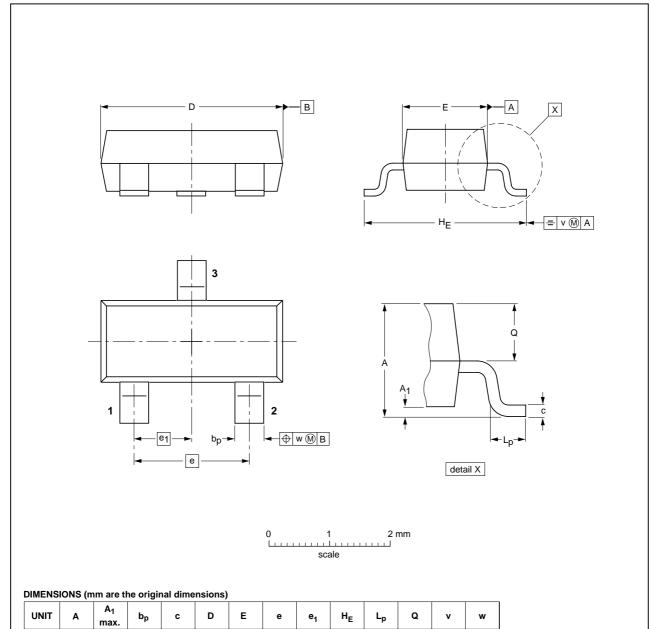
PNP general purpose transistors

BC859; BC860

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT23		TO-236AB				-04-11-04 06-03-16

0.45

0.55

0.1

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0.38

0.9

PNP general purpose transistors

BC859; BC860

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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